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TS3A4751 SCDS227F – JULY 2006 – REVISED MARCH 2015

TS3A4751 0.9-Ω Low-voltage, single-supply, 4-channel spst analog switch

Technical

Documents

1 Features

- Low ON-State Resistance (R_{ON})
 - 0.9 Ω Max (3-V Supply)
 - 1.5 Ω Max (1.8-V Supply)
- R_{ON} Flatness: 0.4 Ω Max (3-V)
- R_{ON} Channel Matching
 - 0.05 Ω Max (3-V Supply)
 - 0.15 Ω Max (1.8-V Supply)
- 1.6-V to 3.6-V Single-Supply Operation
- 1.8-V CMOS Logic Compatible (3-V Supply)
- High Current-Handling Capacity (100 mA Continuous)
- Fast Switching: t_{ON} = 5 ns, t_{OFF} = 4 ns
- Supports Both Digital and Analog Applications
- ESD Protection Exceeds JESD-22
 - ±4000-V Human Body Model (A114-A)
 - 300-V Machine Model (A115-A)
 - ±1000-V Charged-Device Model (C101)

2 Applications

- Power Routing
- Battery-Powered Systems
- Audio and Video Signal Routing
- Low-Voltage Data-Acquisition Systems
- Communications Circuits
- PCMCIA Cards
- Cellular Phones
- Modems
- Hard Drives

3 Description

Tools &

Software

The TS3A4751 device is a bidirectional, 4-channel, normally open (NO) single-pole single-throw (SPST) analog switch that operates from a single 1.6-V to 3.6-V supply. This device has fast switching speeds, handles rail-to-rail analog signals, and consumes very low quiescent power.

Support &

Community

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The digital input is 1.8-V CMOS compatible when using a 3-V supply.

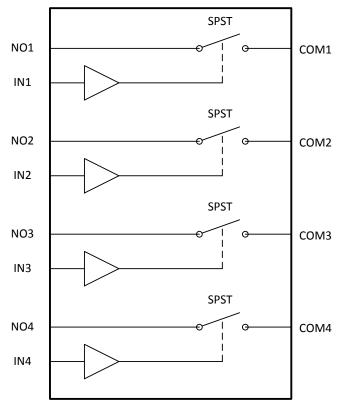
The TS3A4751 device has four normally open (NO) switches. The TS3A4751 is available in a 14-pin thin shrink small-outline package (TSSOP) and in spacesaving 14-pin VQFN (RGY) and micro X2QFN (RUC) packages.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
	TSSOP (14)	5.00 mm × 4.40 mm
TS3A4751	VQFN (14)	3.50 mm × 3.50 mm
	X2QFN (14)	2.00 mm × 2.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



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4 Revision History

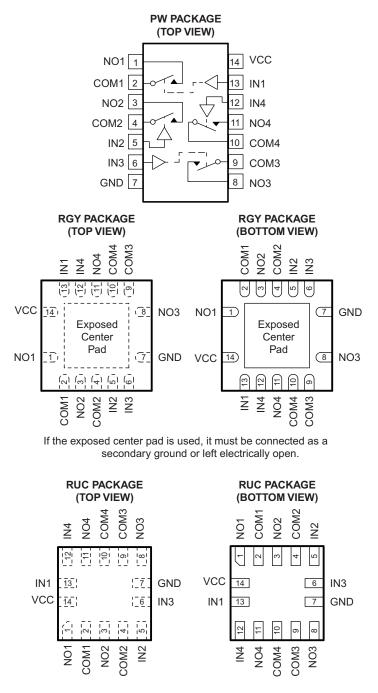
Cł	Changes from Revision E (January 2015) to Revision F Page					
•	Changed Supply Voltage from: 3.3 V to: 3.6 V in the Recommended Operating Conditions	5				
Cł	nanges from Revision D (July 2008) to Revision E	Page				
•	Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional					

Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device

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5 Pin Configuration and Functions



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STRUMENTS

XAS

Pin Functions

	PIN	I/O	DESCRIPTION
NO.	NAME	1/0	DESCRIPTION
1	NO1	I/O	Normally open signal path
2	COM1	I/O	Common signal path
3	NO2	I/O	Normally open signal path
4	COM2	I/O	Common signal path
5	IN2	I	Logic control input
6	IN3	I	Logic control input
7	GND	_	Ground
8	NO3	I/O	Normally open signal path
9	COM3	I/O	Common signal path
10	COM4	I/O	Common signal path
11	NO4	I/O	Normally open signal path
12	IN4	I	Logic control input
13	IN1	I	Logic control input
14	V _{CC}	I	Positive supply voltage

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage referenced to GND ⁽²⁾		-0.3	4	V
V _{NO} V _{COM} V _{IN}	Analog and digital voltage		-0.3	V _{CC} + 0.3	V
I _{NO} I _{COM}	On-state switch current	V_{NO} , $V_{COM} = 0$ to V_{CC}	-100	100	mA
I _{CC} I _{GND}	Continuous current through $V_{\mbox{\scriptsize CC}}$ or $\mbox{\scriptsize GND}$			±100	mA
V	Peak current pulsed at 1 ms, 10% duty cycle	COM, V _{I/O}		±200	mA
T _A	Operating temperature		-40	85	°C
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Signals on COM or NO exceeding V_{CC} or GND are clamped by internal diodes. Limit forward diode current to maximum current rating.

6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 or ANSI/ESDA/JEDEC JS-002 $^{\rm (2)}$	±1000	V
		Machine Model	±300	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{CC}	Supply Voltage	1.65	3.6	V
V _{NO} V _{COM} V _{IN}	Analog and digital voltage range	0	V _{CC}	V

6.4 Thermal Information

			TS3A4751		
	THERMAL METRIC ⁽¹⁾	PW	RGY	RUC	UNIT
			14 PINS	1	
R_{\thetaJA}	Junction-to-ambient thermal resistance	132.3	68.5	196.4	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	60.6	83.1	73.9	
$R_{\theta JB}$	Junction-to-board thermal resistance	74.2	44.6	130.7	°C/W
ΨJT	Junction-to-top characterization parameter	11.2	7.8	2.1	°C/W
Ψјв	Junction-to-board characterization parameter	73.6	44.7	130.6	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	24.6	N/A	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

NSTRUMENTS

EXAS

6.5 Electrical Characteristics for 1.8-V Supply

 $V_{CC} = 1.65$ V to 1.95 V. $T_A = -40^{\circ}$ C to 85°C. $V_{III} = 1$ V. $V_{III} = 0.4$ V (unless otherwise noted)^{(1) (2)}

	PARAMETER	TEST CONDITION	ONS	T _A	MIN	TYP ⁽³⁾	MAX	UNIT
ANALOG S	WITCH						ľ	
V _{COM} , V _{NO}	Analog signal range				0		V _{CC}	V
D		$V_{\rm CC} = 1.8 \text{ V}, I_{\rm COM} = -10 \text{ m/}$	۹.	25°C		1	1.5	0
R _{on}	ON-state resistance	$V_{NO} = 0.9 V$,	Full			2	Ω
	ON-state resistance match	$V_{\rm CC} = 1.8 \text{ V}, I_{\rm COM} = -10 \text{ m/}$	۹.	25°C		0.09	0.15	0
ΔR_{on}	between channels ⁽⁴⁾	$V_{NO} = 0.9 V$,	Full			0.25	Ω
-	ON-state resistance	$V_{CC} = 1.8 \text{ V}, I_{COM} = -10 \text{ m/}$	۹.	25°C		0.7	0.9	0
R _{on(flat)}	flatness ⁽⁵⁾	$0 \le V_{NO} \le V_{CC}$,	Full			1.5	Ω
	NO			25°C	-1	0.5	1	
I _{NO(OFF)}	OFF leakage current ⁽⁶⁾	$V_{\rm NO} = 1.8 \text{ V}, 0.15 \text{ V}$	_{CC} = 1.95 V, V _{COM} = 0.15 V, 1.65 V, _{NO} = 1.8 V, 0.15 V		-10		10	nA
	СОМ	$V_{CC} = 1.95 V. V_{COM} = 0.15$	V _{CC} = 1.95 V, V _{COM} = 0.15 V, 1.65 V,		-1	0.5	1	
I _{COM(OFF)}	OFF leakage current ⁽⁶⁾	$V_{\rm NO} = 1.65 \text{ V}, 0.15 \text{ V}$.,,	Full	-10		10	nA
	СОМ	V _{CC} = 1.95 V, V _{COM} = 0.15	V. 1.65 V.	25°C	-1	0.01	1	
I _{COM(ON)}	ON leakage current ⁽⁶⁾	$V_{\rm NO} = 0.15$ V, 1.65 V, or floa		Full	-3		3	nA
DYNAMIC				I			I	
		$V_{NO} = 1.5 \text{ V}, \text{ R}_{L} = 50 \Omega,$		25°C		6	18	
t _{ON} Turn-on ti	Turn-on time	$C_L = 35 \text{ pF}, \text{ See Figure 1}$		Full			20	ns
		V _{NO} = 1.5 V, R _L = 50 Ω,		25°C		5	10	
t _{OFF}	Turn-off time	$V_{NO} = 1.3 \text{ V}, \text{ KL} = 30 \Omega,$ C _L = 35 pF, See Figure 1		Full			12	ns
Q _C	Charge injection	$V_{GEN} = 0, R_{GEN} = 0, C_L = 1$ See Figure 5	nF,	25°C		3.2		рС
C _{NO(OFF)}	NO OFF capacitance	f = 1 MHz, See Figure 2		25°C		23		pF
C _{COM(OFF)}	COM OFF capacitance	f = 1 MHz, See Figure 2		25°C		20		pF
C _{COM(ON)}	COM ON capacitance	f = 1 MHz, See Figure 2		25°C		43		pF
BW	Bandwidth	$R_L = 50 \Omega$, Switch ON		25°C		123		MHz
•		$R_{L} = 50 \Omega, C_{L} = 5 pF,$	f = 1 MHz			-61		
O _{ISO}	OFF isolation ⁽⁷⁾	See Figure 3	f = 10 MHz	25°C		-36		dB
	0	$R_1 = 50 \Omega, C_1 = 5 pF,$	f = 10 MHz			-95		
X _{TALK}	Crosstalk	See Figure 3	f = 100 MHz	25°C		-73		dB
		f = 20 Hz to 20 kHz, V _{COM}	R _L = 32 Ω			0.14%		
THD	Total harmonic distortion	$= 2 V_{P-P}$	$R_L = 600 \Omega$	25°C		0.013%		
DIGITAL CO	NTROL INPUTS (IN1-IN4)						1	
V _{IH}	Input logic high			Full	1			V
V _{IL}	Input logic low			Full			0.4	V
				25°C		0.1	5	
I _{IN}	Input leakage current	$V_I = 0 \text{ or } V_{CC}$		Full	-10		10	nA
SUPPLY		1			1			
V _{CC}	Power-supply range				1.6		3.6	V
				25°C			0.05	
I _{CC}	Positive-supply current	$V_{I} = 0 \text{ or } V_{CC}$		Full			0.5	μA

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum. (1)

(2) Parts are tested at 85°C and specified by design and correlation over the full temperature range.

Typical values are at $T_A = 25^{\circ}C$. (3)

(4)

 $\Delta r_{on} = r_{on(max)} - r_{on(min)}$ Flatness is defined as the difference between the maximum and minimum value of r_{on} as measured over the specified analog signal (5) ranges.

Leakage parameters are 100% tested at the maximum-rated hot operating temperature and specified by correlation at $T_A = 25^{\circ}$ C. OFF isolation = $20_{log}10$ (V_{COM}/V_{NO}), V_{COM} = output, V_{NO} = input to OFF switch (6)

(7)

6.6 Electrical Characteristics for 3-V Supply

 $V_{CC} = 2.7 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C, $V_{IH} = 1.4 \text{ V}$, $V_{II} = 0.5 \text{ V}$ (unless otherwise noted).⁽¹⁾ ⁽²⁾

	PARAMETER	TEST COND	ITIONS	T _A	MIN	TYP ⁽³⁾	MAX	UNIT	
ANALOG SW	ИТСН								
V _{COM} , V _{NO}	Analog signal range				0		V _{CC}	V	
	ON state we sister as	$V_{CC} = 2.7 \text{ V}, I_{COM} = -1$	00 mA,	25°C		0.7	0.9	0	
R _{on}	ON-state resistance	$V_{\rm NO} = 1.5 {\rm V}$		Full			1.1	Ω	
	ON-state resistance match	$V_{CC} = 2.7 \text{ V}, I_{COM} = -1$	00 mA,	25°C		0.03	0.05	0	
ΔR_{on}	between channels ⁽⁴⁾	$V_{NO} = 1.5 V$	V _{NO} = 1.5 V				0.15	Ω	
D	ON-state resistance	$V_{\rm CC} = 2.7 \text{ V}, I_{\rm COM} = -100 \text{ mA},$		25°C		0.23	0.4	Ω	
R _{on(flat)}	flatness ⁽⁵⁾	$V_{\rm NO} = 1 \text{ V}, 1.5 \text{ V}, 2 \text{ V}$		Full			0.5	Ω	
1	NO	$V_{CC} = 3.6 \text{ V}, V_{COM} = 0.3 \text{ V}, 3 \text{ V},$		25°C	-2	1	2	nA	
NO(OFF)	OFF leakage current ⁽⁶⁾	$V_{NO} = 3 V, 0.3 V$		Full	-18		18	ΠA	
1	COM	$V_{CC} = 3.6 \text{ V}, V_{COM} = 0$.3 V, 3 V,	25°C	-2	1	2	nA	
COM(OFF)	OFF leakage current ⁽⁶⁾	$V_{NO} = 3 V, 0.3 V$		Full	-18		18	IIA	
1	СОМ	$V_{CC} = 3.6 \text{ V}, V_{COM} = 0.3 \text{ V}, 3 \text{ V},$.3 V, 3 V,	25°C	-2.5	0.01	2.5	nA	
COM(ON)	ON leakage current ⁽⁶⁾	$V_{NO} = 0.3 V, 3 V, or flo$		Full	-5		5	ΠA	
DYNAMIC									
	Turn-on time	$V_{NO} = 1.5 \text{ V}, \text{ R}_{\text{L}} = 50 \text{ G}$	۵,	25°C		5	14	20	
t _{ON}	$C_L = 35 \text{ pF}, \text{ See Figure 1}$		• 1	Full			15	ns	
	Turn-off time	$V_{NO} = 1.5 \text{ V}, \text{ R}_{\text{L}} = 50 \text{ G}$	Ω,	25°C		4	9		
toff		$C_L = 35 \text{ pF}$, See Figure 1		Full			10	ns	
Q _C	Charge injection	$V_{GEN} = 0, R_{GEN} = 0, C_L$ See Figure 5	_ = 1 nF,	25°C		3		рС	
C _{NO(OFF)}	NO OFF capacitance	f = 1 MHz, See Figure 2	2	25°C		23		pF	
C _{COM(OFF)}	COM OFF capacitance	f = 1 MHz, See Figure 2	2	25°C		20		pF	
C _{COM(ON)}	COM ON capacitance	f = 1 MHz, See Figure 2	2	25°C		43		pF	
BW	Bandwidth	$R_L = 50 \Omega$, Switch ON		25°C		125		MHz	
0	OFF isolation ⁽⁷⁾	$R_L = 50 \Omega, C_L = 5 pF,$	f = 10 MHz	25°C		-40		dB	
O _{ISO}	OFF ISUIALION V	See Figure 3	f = 1 MHz	25 0		-62		uВ	
v	Crosstalk	$R_{L} = 50 \Omega, C_{L} = 5 pF,$	f = 10 MHz	25°C -		-73		dB	
X _{TALK}	CIUSSIAIK	See Figure 3	f = 1 MHz	25 0		-95		uВ	
THD	Total harmonic distortion	f = 20 Hz to 20 kHz,	$R_L = 32 \Omega$	25°C		0.04%			
	$V_{COM} = 2 V_{P-P}$ $R_L = 6$		$R_L = 600 \ \Omega$	23 0		0.003%			
	NTROL INPUTS (IN1–IN4)	- 1							
V _{IH}	Input logic high			Full	1.4			V	
V _{IL}	Input logic low			Full			0.5	V	
 I	Input leakage current	$V_{I} = 0 \text{ or } V_{CC}$		25°C		0.5		۳۸	
I _{IN}	mpul leakage culteril			Full	-20		20	nA	
SUPPLY									
V _{CC}	Power-supply range				1.6		3.6	V	
	Desitive supply surrest			25°C			0.075	5 ^	
I _{CC}	Positive-supply current	$V_{CC} = 3.6 \text{ V}, \text{ V}_{IN} = 0 \text{ or}$	V CC	Full			0.75	μA	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

(2) Parts are tested at 85°C and specified by design and correlation over the full temperature range.

Typical values are at $V_{CC} = 3 \text{ V}$, $T_A = 25^{\circ}\text{C}$. (3)

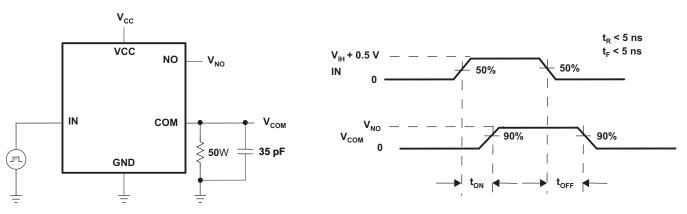
(4)

 $\Delta r_{on} = r_{on(max)} - r_{on(min)}$ Flatness is defined as the difference between the maximum and minimum value of r_{on} as measured over the specified analog signal (5) ranges.

Leakage parameters are 100% tested at the maximum-rated hot operating temperature and specified by correlation at $T_A = 25^{\circ}$ C. OFF isolation = $20_{log}10$ (V_{COM}/V_{NO}), V_{COM} = output, V_{NO} = input to OFF switch (6)

(7)







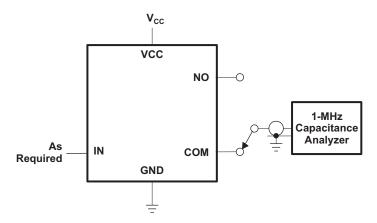
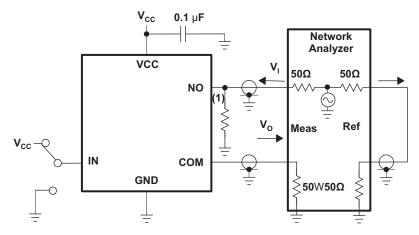


Figure 2. NO and COM Capacitance



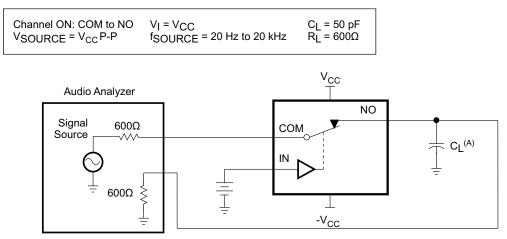
Measurements are standardized against short at socket terminals. OFF isolation is measured between COM and OFF terminals on each switch. Bandwidth is measured between COM and ON terminals on each switch. Signal direction through switch is reversed; worst values are recorded. OFF isolation = 20 log V_0/V_1

 $^{(1)}\text{Add}$ 50- Ω termination for OFF isolation

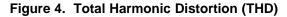


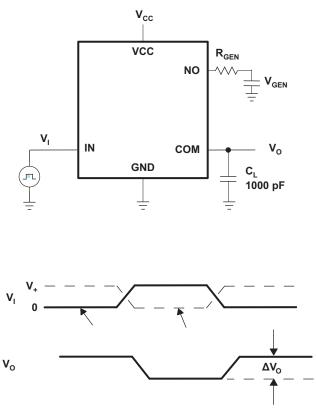


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A. C_L includes probe and jig capacitance.





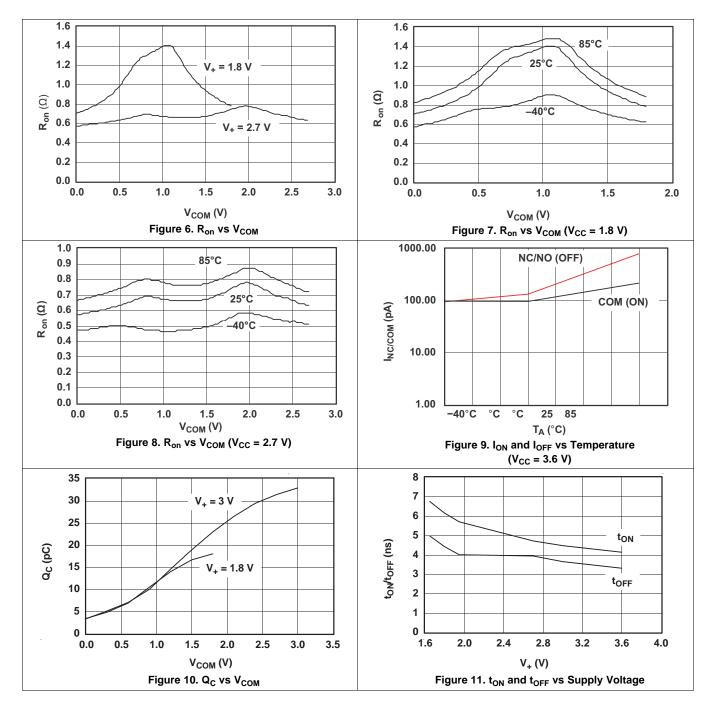


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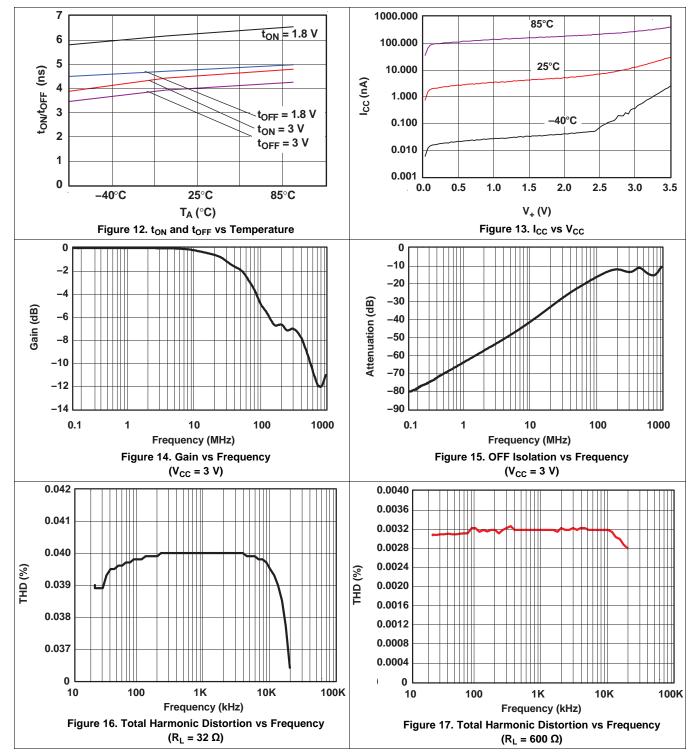
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6.7 Typical Characteristics





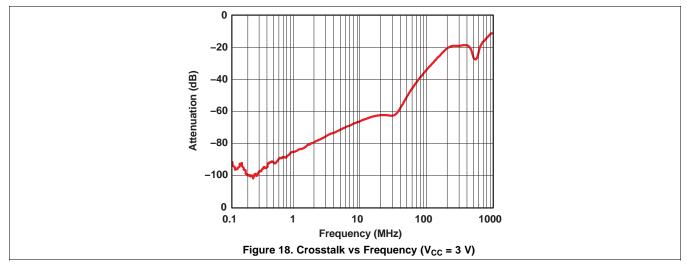
Typical Characteristics (continued)



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Typical Characteristics (continued)





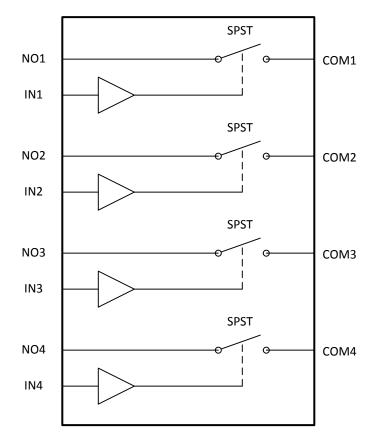
7 Detailed Description

The TS3A4751 is a bidirectional, 4-channel, normally open (NO) single-pole single-throw (SPST) analog switch that operates from a single 1.6-V to 3.6-V supply. This device has fast switching speeds, handles rail-to-rail analog signals, and consumes very low quiescent power.

The digital input is 1.8-V CMOS compatible when using a 3-V supply.

The TS3A4751 has four normally open (NO) switches. The TS3A4751 is available in a 14-pin thin shrink smalloutline package (TSSOP) and in space-saving 14-pin VQFN (RGY) and micro X2QFN (RUC) packages.

7.2 Functional Block Diagram



7.3 Feature Description

This device has fast switching speeds, handles rail-to-rail analog signals, and consumes very low quiescent power.

The digital input is 1.8-V TTL/CMOS compatible when using a 3-V supply.

7.4 Device Functional Modes

Table 1. Function Table

IN	NO TO COM, COM TO NO
L	OFF
Н	ON

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

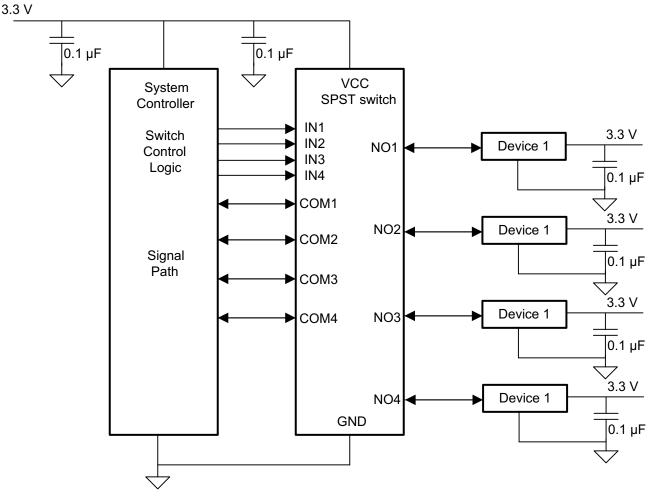
8.1.1 Logic Inputs

The TS3A4751 logic inputs can be driven up to 3.6 V, regardless of the supply voltage. For example, with a 1.8-V supply, IN may be driven low to GND and high to 3.6 V. Driving IN rail to rail minimizes power consumption.

8.1.2 Analog Signal Levels

Analog signals that range over the entire supply voltage (V_{CC} to GND) can be passed with very little change in R_{on} (see *Typical Characteristics*). The switches are bidirectional, so NO and COM can be used as either inputs or outputs.

8.2 Typical Application







Typical Application (continued)

8.2.1 Design Requirements

Ensure that all of the signals passing through the switch are with in the specified ranges to ensure proper performance.

8.2.2 Detailed Design Procedure

The TS3A4751 and can be properly operated without any external components. However, it is recommended that unused pins should be connected to ground through a 50- Ω resistor to prevent signal reflections back into the device. It is also recommended that the digital control pins (INX) be pulled up to V_{CC} or down to GND to avoid undesired switch positions that could result from the floating pin.

8.2.3 Application Curve

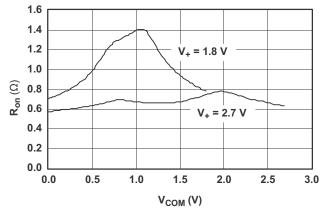


Figure 20. Ron vs V_{COM}

9 Power Supply Recommendations

Proper power-supply sequencing is recommended for all CMOS devices. Do not exceed the absolute maximum ratings because stresses beyond the listed ratings can cause permanent damage to the devices. Always sequence V_{CC} on first, followed by NO or COM.

Although it is not required, power-supply bypassing improves noise margin and prevents switching noise propagation from the V_{CC} supply to other components. A 0.1- μ F capacitor, connected from V_{CC} to GND, is adequate for most applications.

10 Layout

10.1 Layout Guidelines

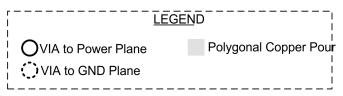
High-speed switches require proper layout and design procedures for optimum performance.

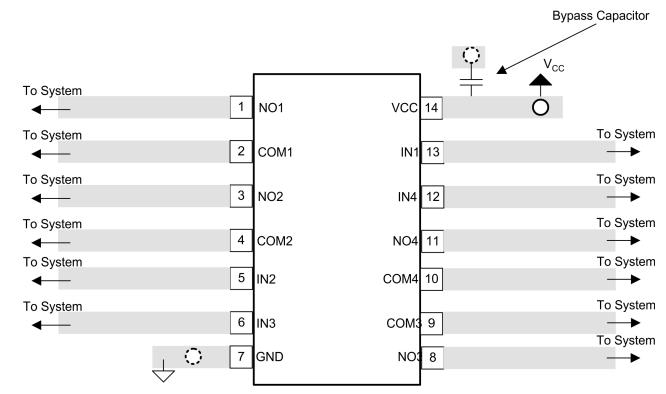
Reduce stray inductance and capacitance by keeping traces short and wide.

Ensure that bypass capacitors are as close to the device as possible.

Use large ground planes where possible.

10.2 Layout Example









11 Device and Documentation Support

11.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.3 Trademarks

E2E is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

11.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TS3A4751PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YC751	Samples
TS3A4751PWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YC751	Samples
TS3A4751RGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YC751	Samples
TS3A4751RUCR	ACTIVE	QFN	RUC	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	3MO	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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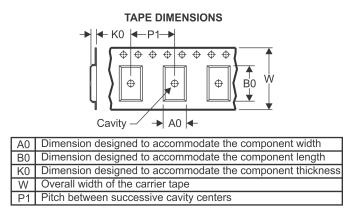
PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3A4751PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TS3A4751RGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1
TS3A4751RUCR	QFN	RUC	14	3000	179.0	8.4	2.25	2.25	0.55	4.0	8.0	Q2

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

5-Jan-2021



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3A4751PWR	TSSOP	PW	14	2000	853.0	449.0	35.0
TS3A4751RGYR	VQFN	RGY	14	3000	853.0	449.0	35.0
TS3A4751RUCR	QFN	RUC	14	3000	200.0	183.0	25.0

MECHANICAL DATA



- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- earrow Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated.
- The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.



RGY (S-PVQFN-N14)

PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: All linear dimensions are in millimeters





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.

D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.

- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



A. An integration of the information o

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

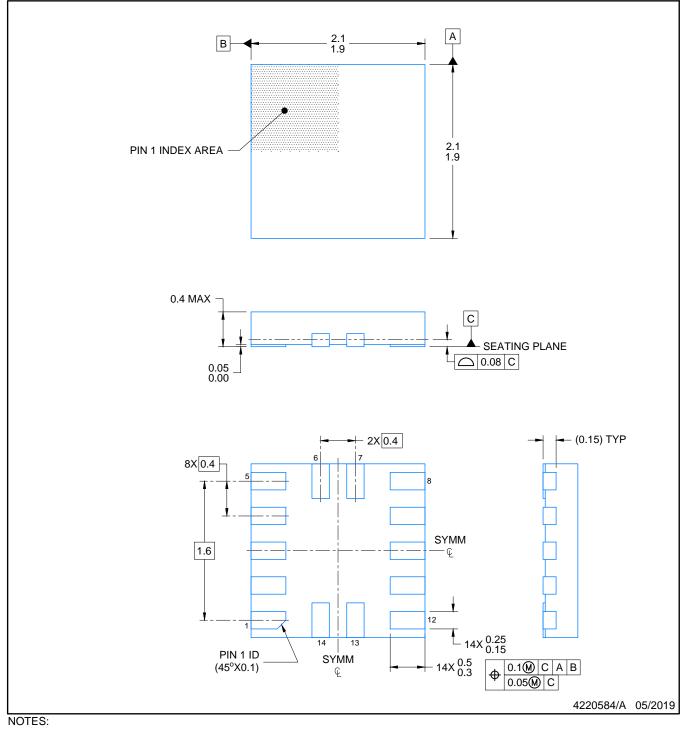


RUC0014A

PACKAGE OUTLINE

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.

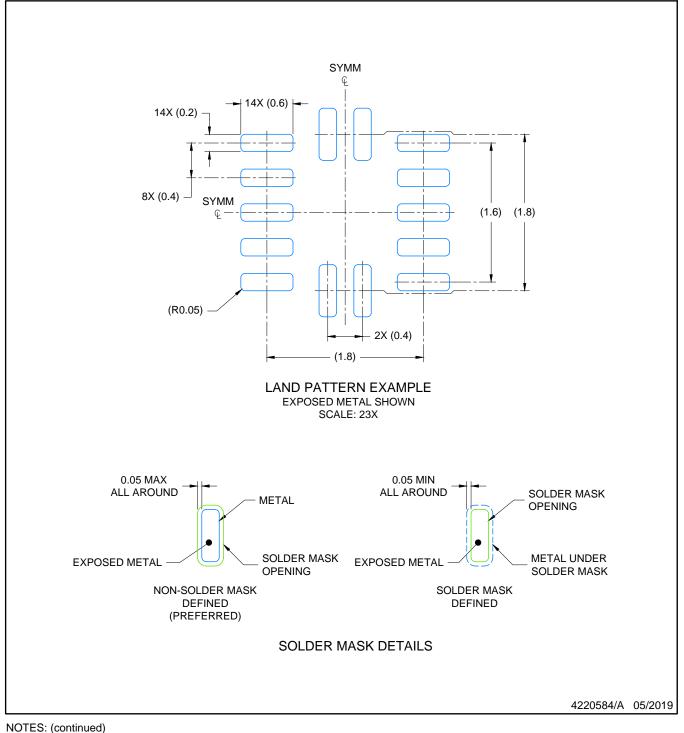


RUC0014A

EXAMPLE BOARD LAYOUT

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

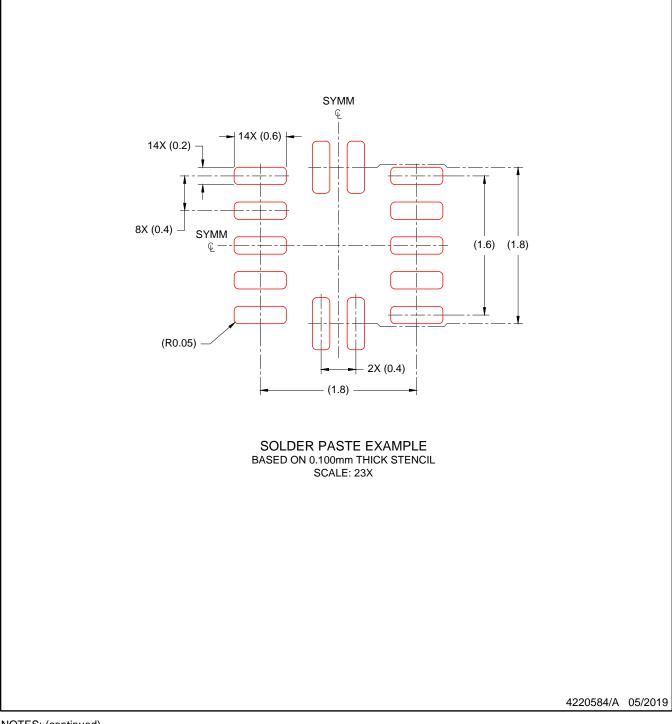


RUC0014A

EXAMPLE STENCIL DESIGN

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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